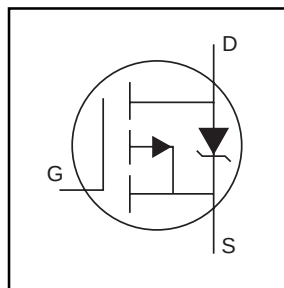


- Ultra Low On-Resistance
- P-Channel
- Surface Mount (IRFR9120N)
- Straight Lead (IRFU9120N)
- Advanced Process Technology
- Fast Switching
- Fully Avalanche Rated



$$V_{DS} = -100V$$

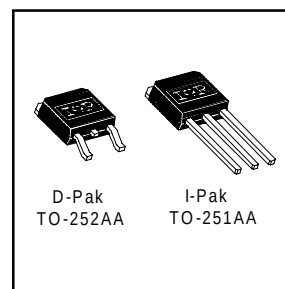
$$R_{DS(on)} = 0.48\Omega$$

$$I_D = -6.6A$$

Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The D-Pak is designed for surface mounting using vapor phase, infrared, or wave soldering techniques. The straight lead version (IRFU series) is for through-hole mounting applications. Power dissipation levels up to 1.5 watts are possible in typical surface mount applications.



D-Pak
TO-252AA

I-Pak
TO-251AA

Absolute Maximum Ratings

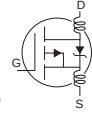
	Parameter	Max.	Units
I_D @ $T_C = 25^\circ C$	Continuous Drain Current, V_{GS} @ -10V	-6.6	A
I_D @ $T_C = 100^\circ C$	Continuous Drain Current, V_{GS} @ -10V	-4.2	
I_{DM}	Pulsed Drain Current ①	-26	
P_D @ $T_C = 25^\circ C$	Power Dissipation	40	W
	Linear Derating Factor	0.32	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy②	100	mJ
I_{AR}	Avalanche Current①	-6.6	A
E_{AR}	Repetitive Avalanche Energy①	4.0	mJ
dv/dt	Peak Diode Recovery dv/dt ③	-5.0	V/ns
T_J	Operating Junction and	-55 to + 150	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	3.1	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB mount)**	—	50	
$R_{\theta JA}$	Junction-to-Ambient	—	110	

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-100	—	—	V	$V_{GS} = 0V$, $I_D = -250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	-0.11	—	$V/^\circ\text{C}$	Reference to 25°C , $I_D = -1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.48	Ω	$V_{GS} = -10V$, $I_D = -3.9A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	-2.0	—	-4.0	V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$
g_{fs}	Forward Transconductance	1.4	—	—	S	$V_{DS} = -50V$, $I_D = -4.0A$ ⑥
I_{DSS}	Drain-to-Source Leakage Current	—	—	-25	μA	$V_{DS} = -100V$, $V_{GS} = 0V$
		—	—	-250		$V_{DS} = -80V$, $V_{GS} = 0V$, $T_J = 150^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$
Q_g	Total Gate Charge	—	—	27	nC	$I_D = -4.0A$
Q_{gs}	Gate-to-Source Charge	—	—	5.0		$V_{DS} = -80V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	15		$V_{GS} = -10V$, See Fig. 6 and 13 ④ ⑥
$t_{d(on)}$	Turn-On Delay Time	—	14	—	ns	$V_{DD} = -50V$
t_r	Rise Time	—	47	—		$I_D = -4.0A$
$t_{d(off)}$	Turn-Off Delay Time	—	28	—		$R_G = 12\Omega$
t_f	Fall Time	—	31	—		$R_D = 12\Omega$, See Fig. 10 ④ ⑥
L_D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact ⑤
L_S	Internal Source Inductance	—	7.5	—		
C_{iss}	Input Capacitance	—	350	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	110	—		$V_{DS} = -25V$
C_{rss}	Reverse Transfer Capacitance	—	70	—		$f = 1.0MHz$, See Fig. 5 ⑥



Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	-6.6	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	-26		
V_{SD}	Diode Forward Voltage	—	—	-1.6	V	$T_J = 25^\circ\text{C}$, $I_S = -3.9A$, $V_{GS} = 0V$ ④
t_{rr}	Reverse Recovery Time	—	100	150	ns	$T_J = 25^\circ\text{C}$, $I_F = -4.0A$
Q_{rr}	Reverse Recovery Charge	—	420	630	nC	$di/dt = 100A/\mu s$ ④ ⑥
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$)				

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)

② Starting $T_J = 25^\circ\text{C}$, $L = 13mH$
 $R_G = 25\Omega$, $I_{AS} = -3.9A$. (See Figure 12)

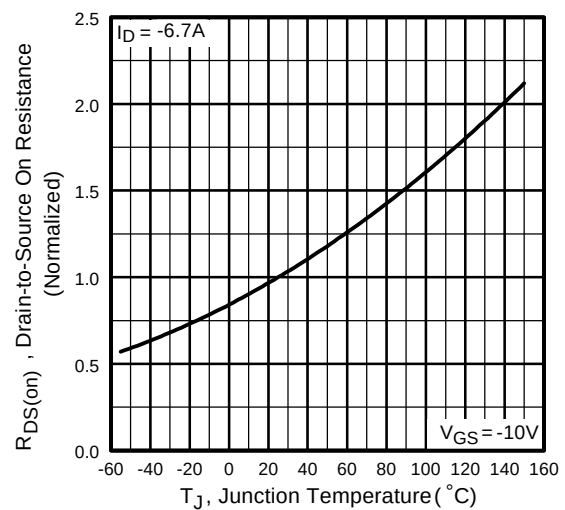
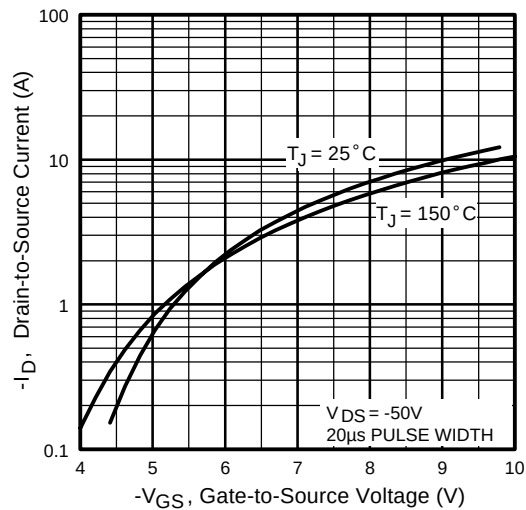
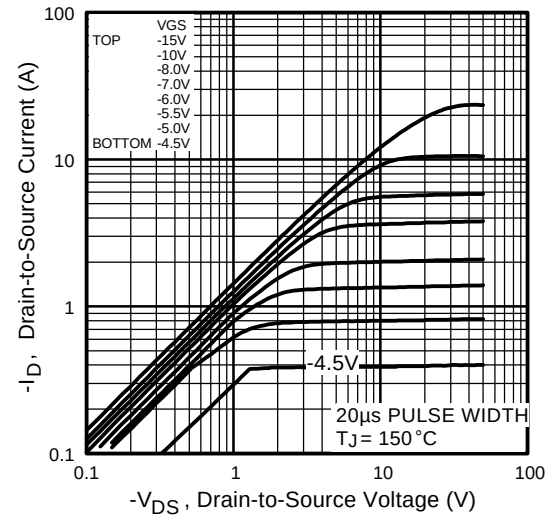
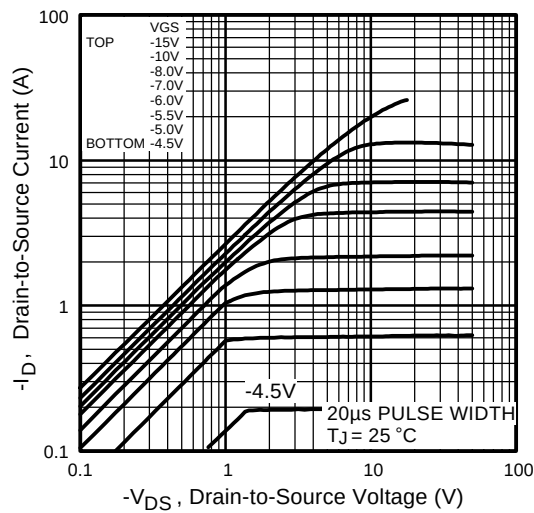
③ $I_{SD} \leq -4.0A$, $di/dt \leq 300A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$,
 $T_J \leq 150^\circ\text{C}$

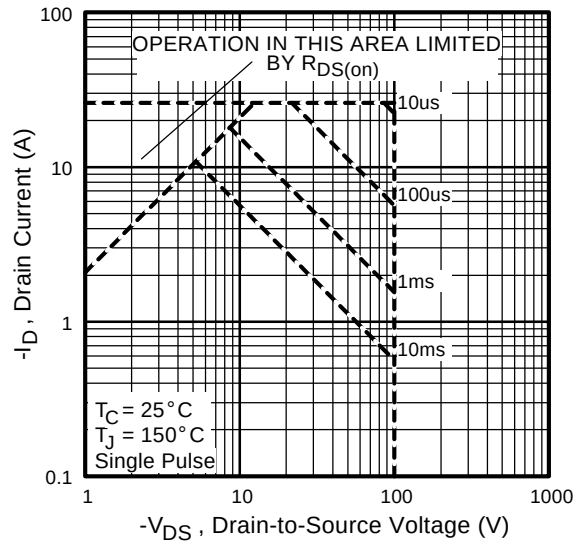
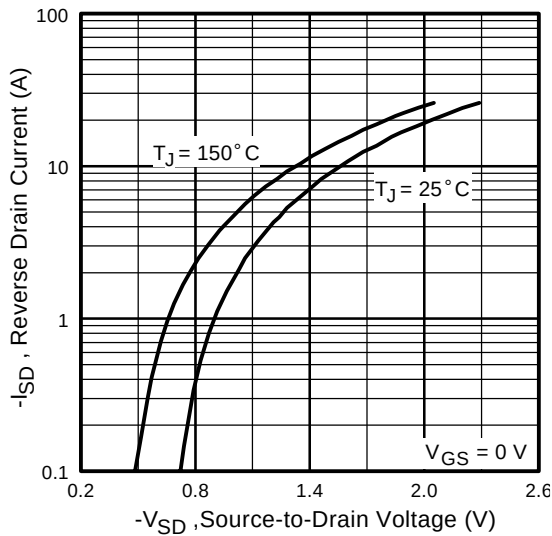
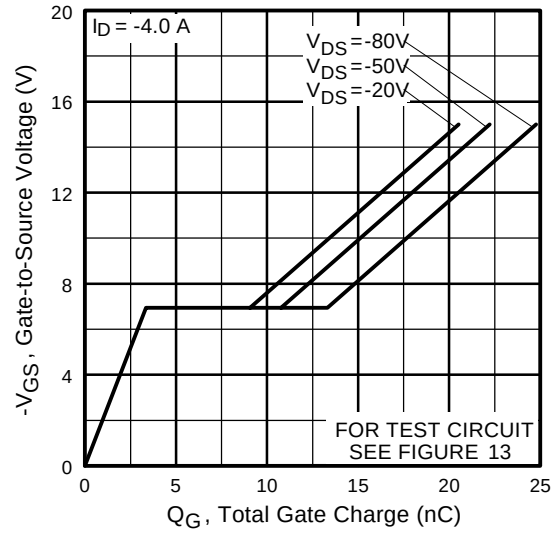
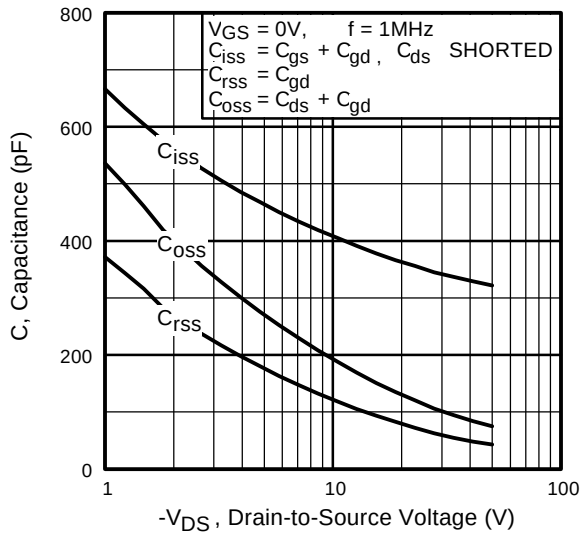
④ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.

⑤ This is applied for I-PAK, L_S of D-PAK is measured between lead and center of die contact

⑥ Uses IRF9520N data and test conditions.

** When mounted on 1" square PCB (FR-4 or G-10 Material) .
For recommended footprint and soldering techniques refer to application note #AN-994





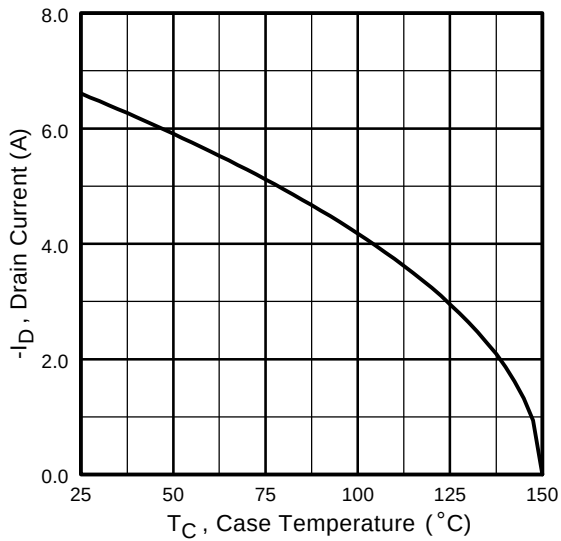


Fig 9. Maximum Drain Current Vs. Case Temperature

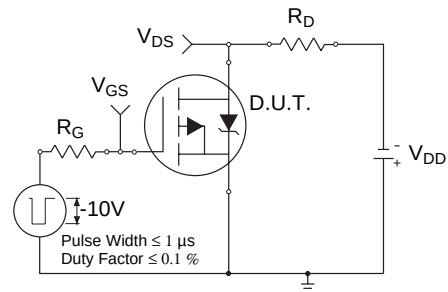


Fig 10a. Switching Time Test Circuit

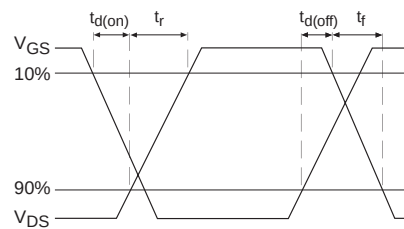


Fig 10b. Switching Time Waveforms

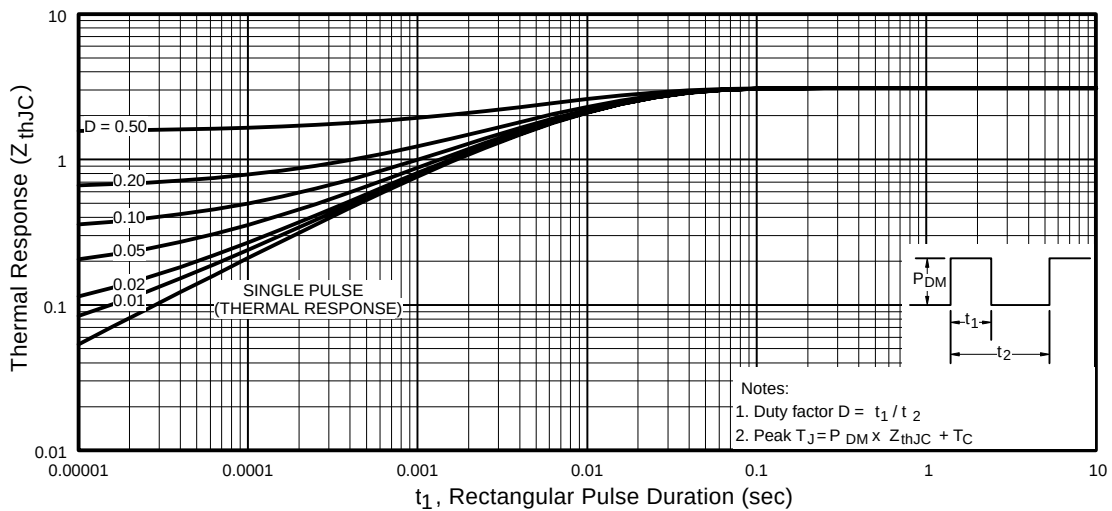


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

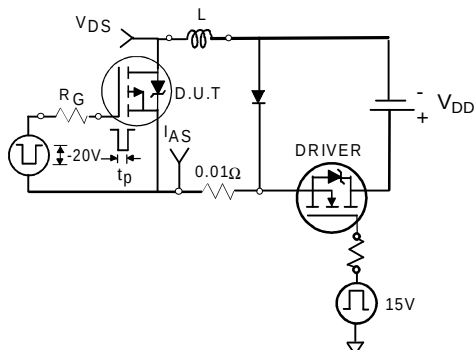


Fig 12a. Unclamped Inductive Test Circuit

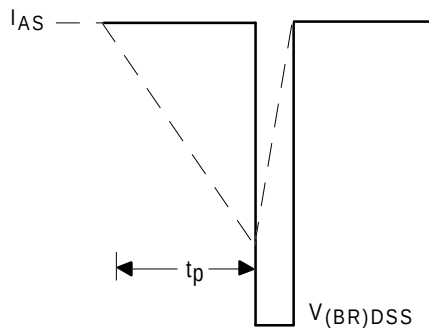


Fig 12b. Unclamped Inductive Waveforms

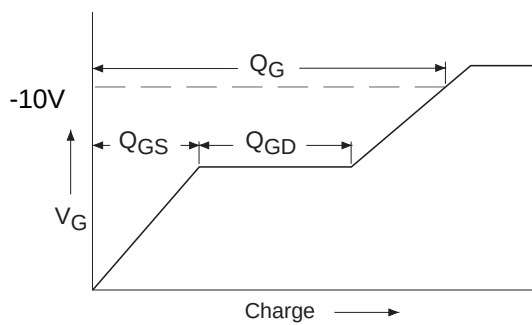


Fig 13a. Basic Gate Charge Waveform

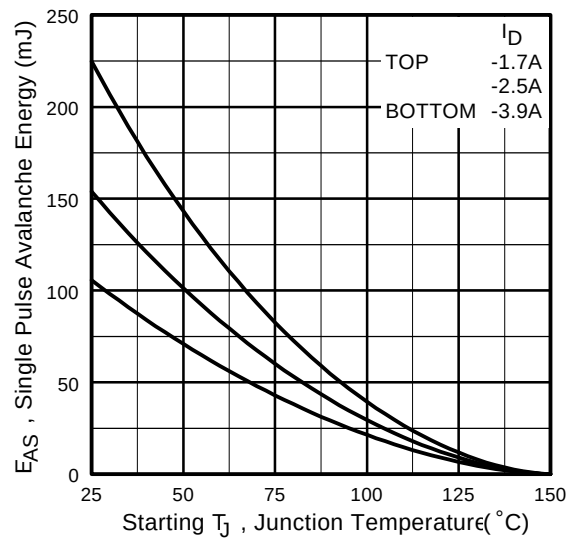


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

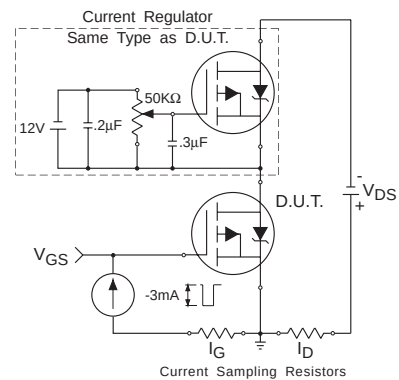
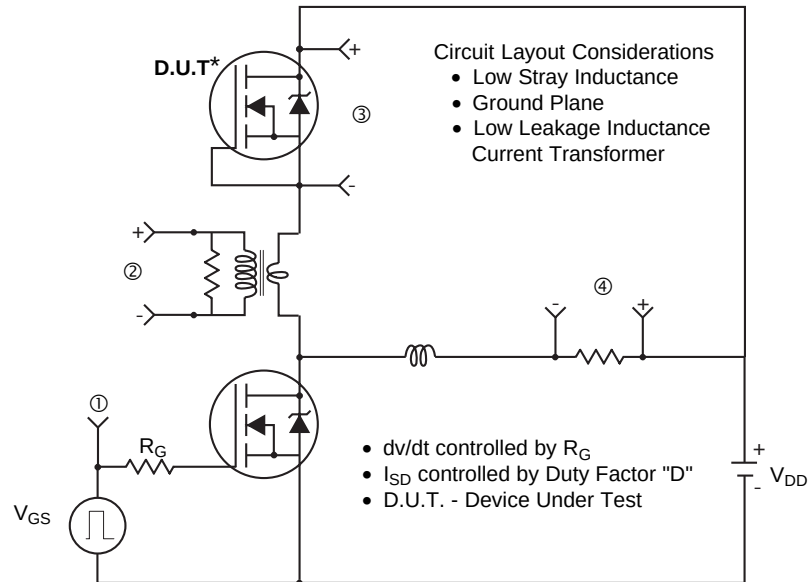
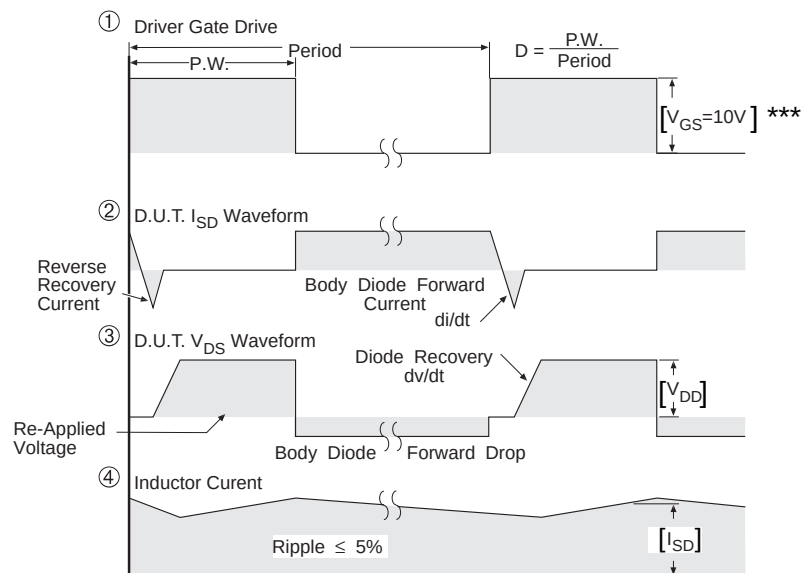


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



* Reverse Polarity of D.U.T for P-Channel

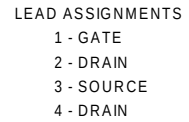


*** $V_{GS} = 5.0V$ for Logic Level and 3V Drive Devices

Fig 14. For P-Channel HEXFETS

International
IOR Rectifier

Dimensions are shown in millimeters (inches)



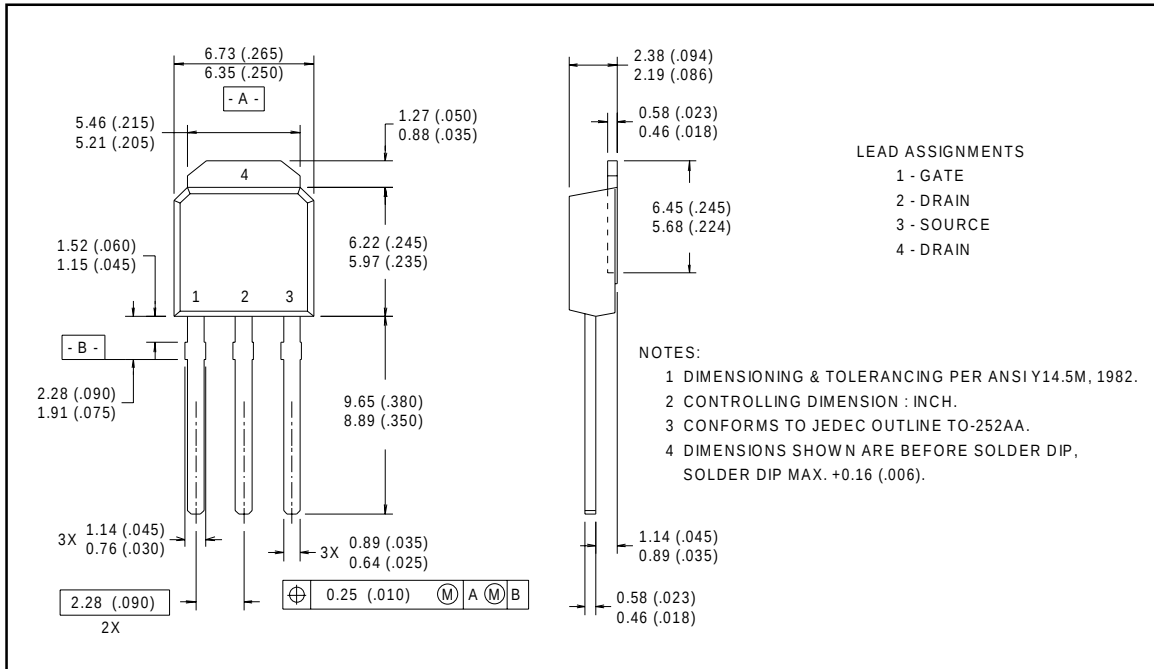
TO-252AA (D-Pak)

SECOND PORTION
OF PART NUMBER

Package Outline

TO-251AA Outline

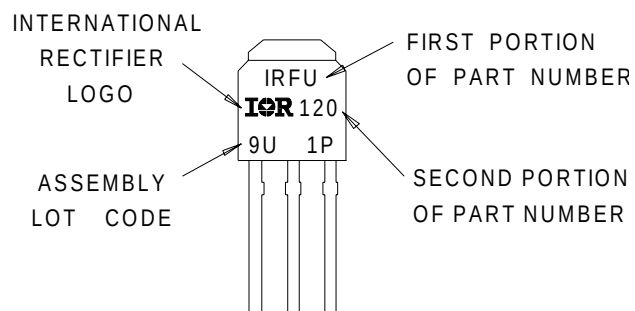
Dimensions are shown in millimeters (inches)



Part Marking Information

TO-251AA (I-Pak)

EXAMPLE : THIS IS AN IRFU120
WITH ASSEMBLY
LOT CODE 9U1P

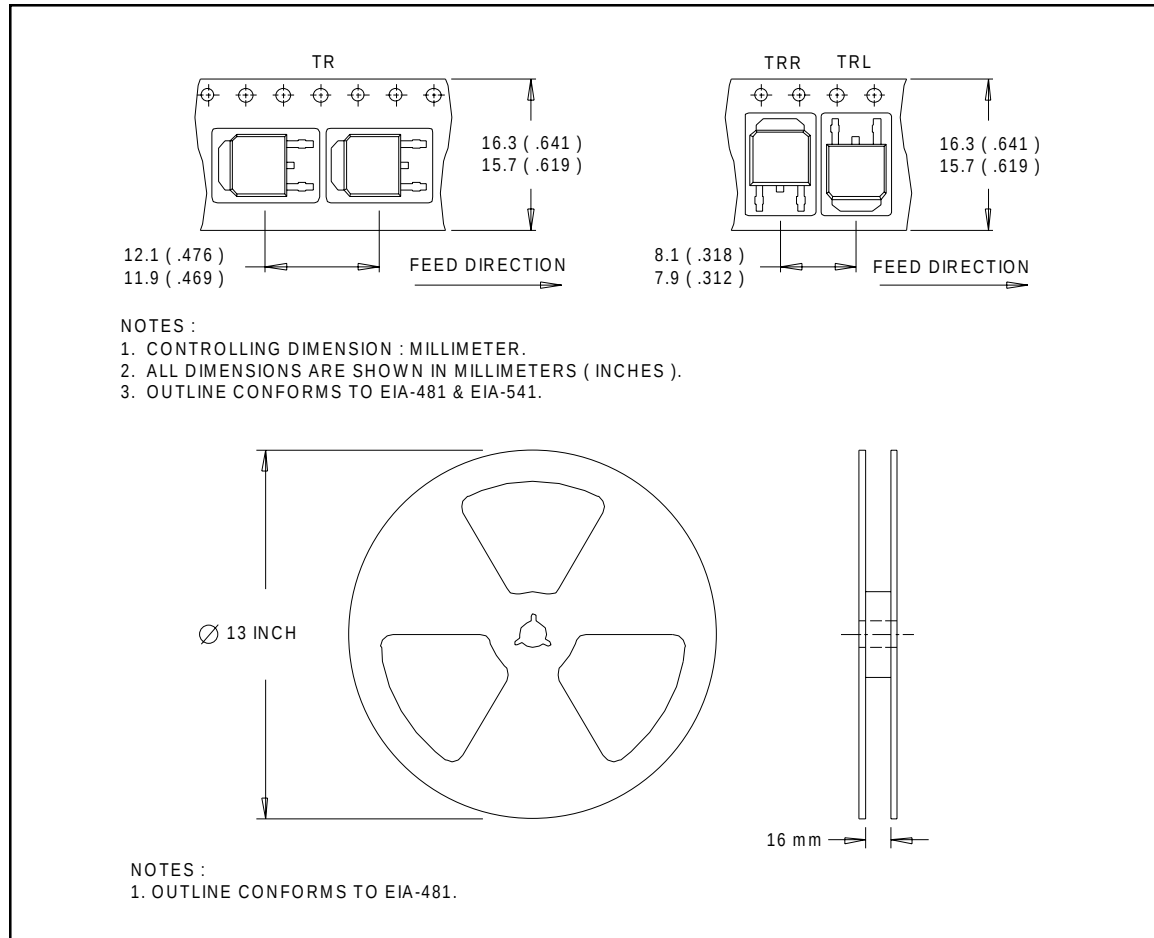


IRFR/U9120N

International
IOR Rectifier

Tape & Reel Information

TO-252AA



International
IOR Rectifier

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EUROPEAN HEADQUARTERS: Hurst Green, Oxted, Surrey RH8 9BB, UK Tel: ++ 44 1883 732020

IR CANADA: 7321 Victoria Park Ave., Suite 201, Markham, Ontario L3R 2Z8, Tel: (905) 475 1897

IR GERMANY: Saalburgstrasse 157, 61350 Bad Homburg Tel: ++ 49 6172 96590

IR ITALY: Via Liguria 49, 10071 Borgaro, Torino Tel: ++ 39 11 451 0111

IR FAR EAST: K&H Bldg., 2F, 30-4 Nishi-Ikebukuro 3-Chome, Toshima-Ku, Tokyo Japan 171 Tel: 81 3 3983 0086

IR SOUTHEAST ASIA: 315 Outram Road, #10-02 Tan Boon Liat Building, Singapore 0316 Tel: 65 221 8371

<http://www.irf.com/> Data and specifications subject to change without notice. 3/98

Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>